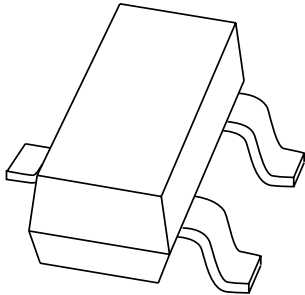


DATA SHEET



BAV199 Low-leakage double diode

Product specification
Supersedes data of 1999 May 11

2001 Oct 12

Low-leakage double diode

BAV199

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μ s
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

- Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are connected in series.

MARKING

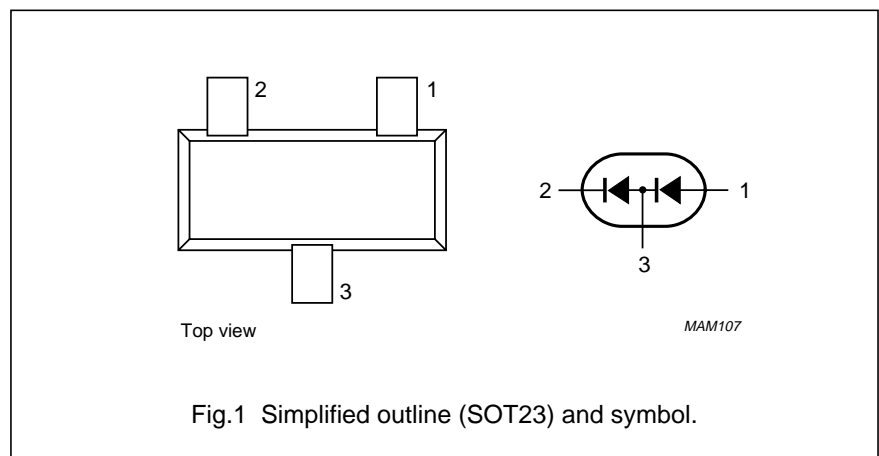
TYPE NUMBER	MARKING CODE ⁽¹⁾
BAV199	JY*

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	anode; cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; note 1; see Fig.2	–	160	mA
		double diode loaded; note 1; see Fig.2	–	140	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge; see Fig.4			
		$t_p = 1\text{ }\mu\text{s}$	–	4	A
		$t_p = 1\text{ ms}$	–	1	A
		$t_p = 1\text{ s}$	–	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$

Note

1. Device mounted on a FR4 printed-circuit board.

Low-leakage double diode

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ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	900	mV
		$I_F = 10\text{ mA}$	–	1000	mV
		$I_F = 50\text{ mA}$	–	1100	mV
		$I_F = 150\text{ mA}$	–	1250	mV
I_R	reverse current	see Fig.5			
		$V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	3	80	nA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	0.8	3	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

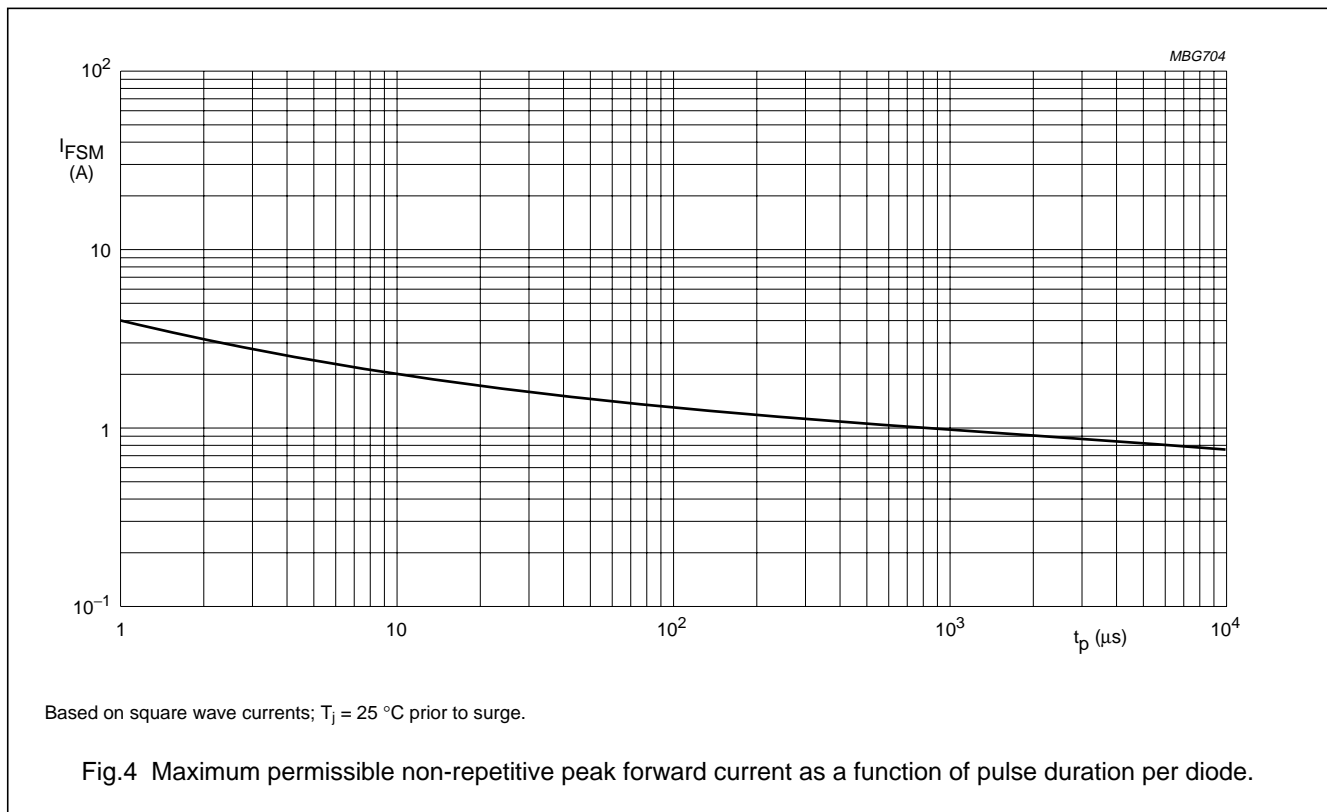
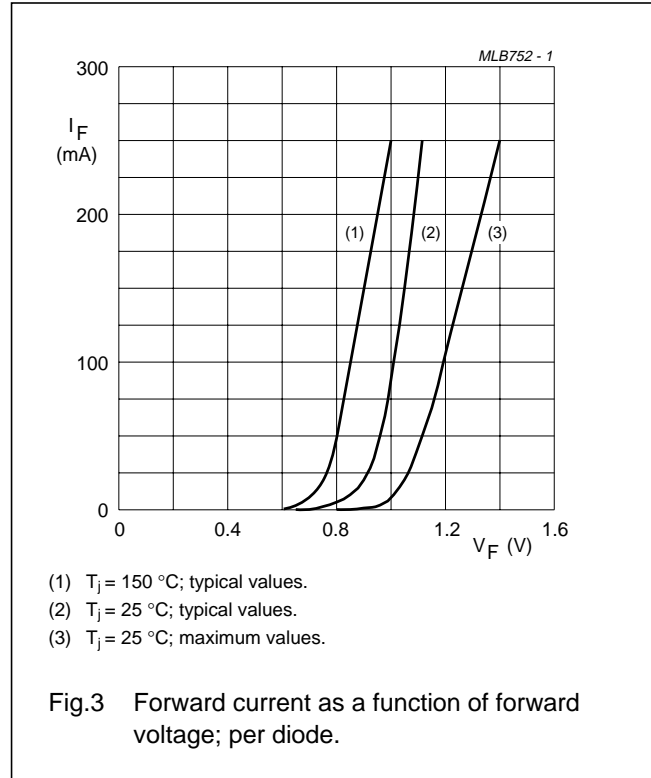
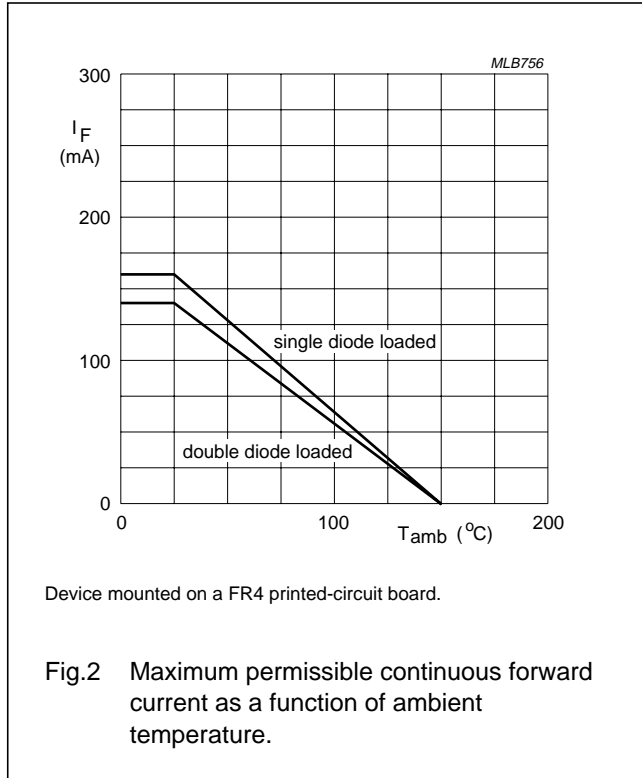
Note

1. Device mounted on a FR4 printed-circuit board.

Low-leakage double diode

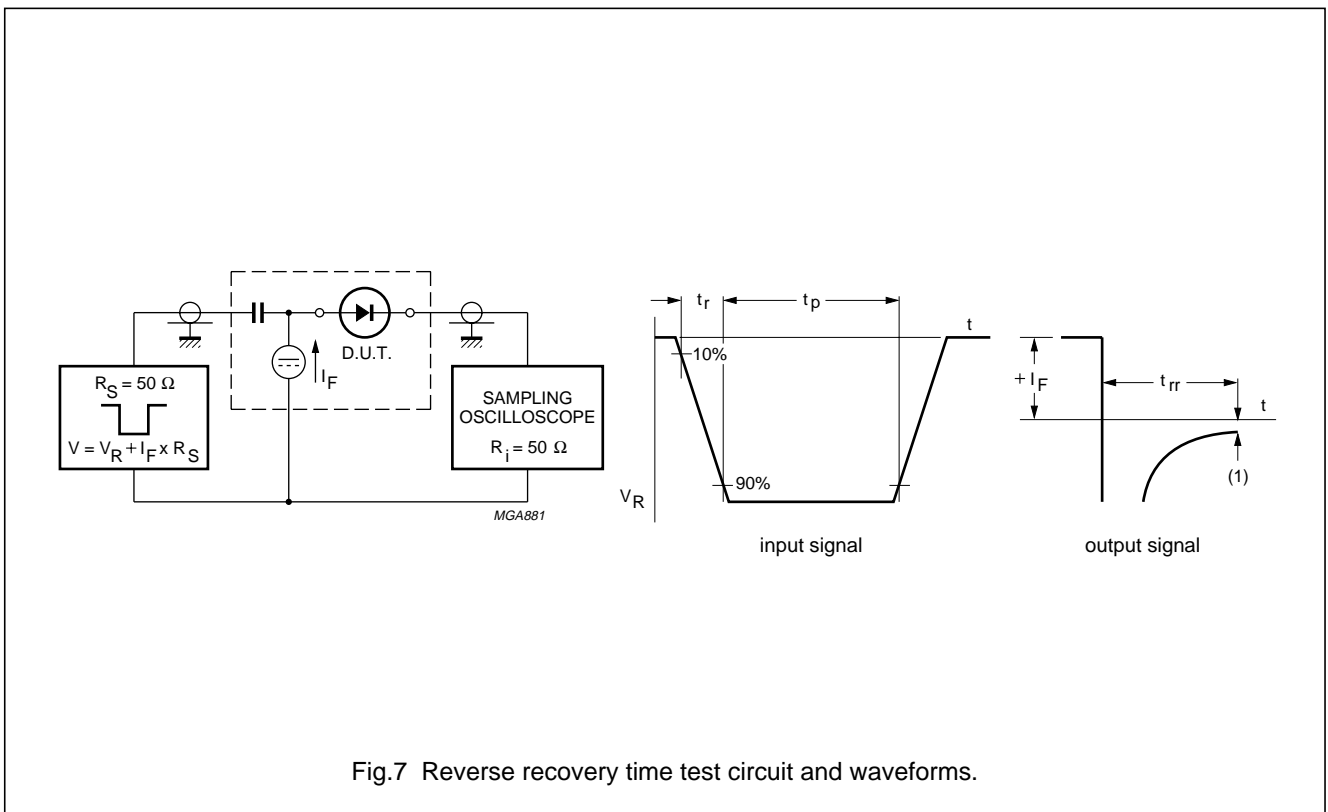
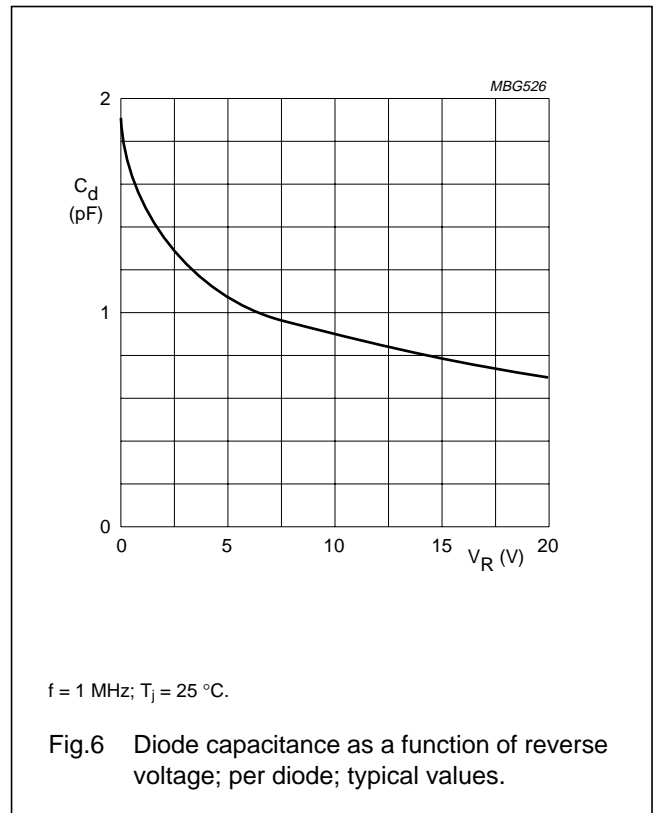
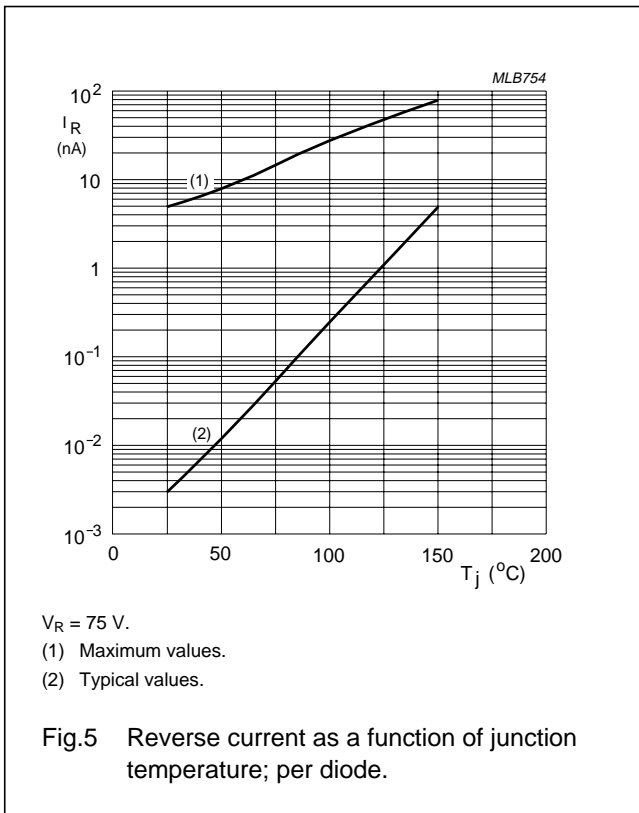
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GRAPHICAL DATA



Low-leakage double diode

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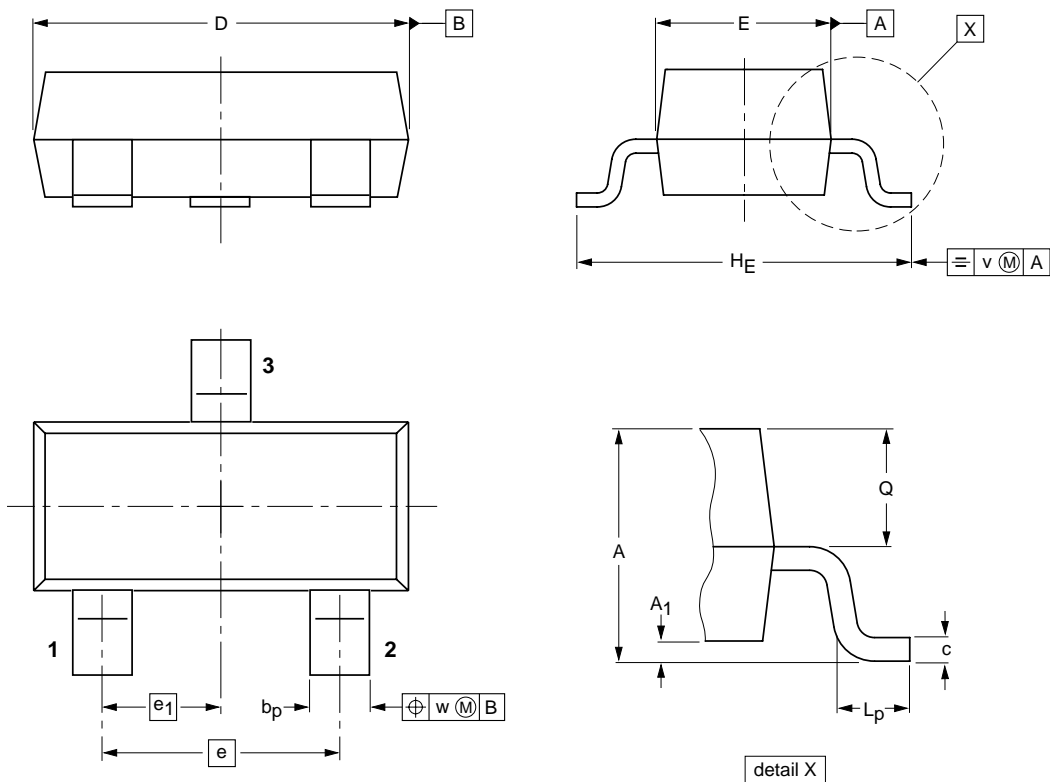
Low-leakage double diode

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT23		TO-236AB			97-02-28 99-09-13

Low-leakage double diode

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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